

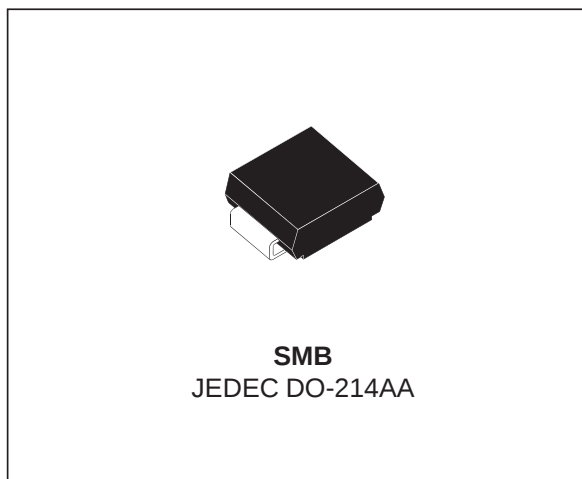
LOW DROP POWER SCHOTTKY RECTIFIER

MAIN PRODUCT CHARACTERISTICS

I_{F(AV)}	2 A
V_{RRM}	25 V
T_j (max)	150 °C
V_F (max)	0.375 V

FEATURES AND BENEFITS

- VERY LOW FORWARD VOLTAGE DROP FOR LESS POWER DISSIPATION
- OPTIMIZED CONDUCTION/REVERSE LOSSES TRADE-OFF WHICH MEANS THE HIGHEST EFFICIENCY IN THE APPLICATIONS
- AVALANCHE CAPABILITY SPECIFIED



DESCRIPTION

Single Schottky rectifier suited to Switched Mode Power Supplies and high frequency DC to DC converters.

Packaged in SMB (JEDEC DO214-AA), this device is especially intended for use in parallel with MOSFETs in synchronous rectification.

ABSOLUTE RATINGS (limiting values)

Symbol	Parameter		Value	Unit
V _{RRM}	Repetitive peak reverse voltage		25	V
I _{F(RMS)}	RMS forward current		10	A
I _{F(AV)}	Average forward current	T _L = 125°C δ = 0.5	2	A
I _{FSM}	Surge non repetitive forward current	tp = 10 ms Sinusoidal	75	A
I _{RRM}	Repetitive peak reverse current	tp=2 μs square F=1kHz	1	A
I _{RSM}	Non repetitive peak reverse current	tp = 100 μs square	1	A
P _{ARM}	Repetitive peak avalanche power	tp = 1μs T _j = 25°C	1500	W
T _{stg}	Storage temperature range		- 65 to + 150	°C
T _j	Maximum operating junction temperature *		150	°C
dV/dt	Critical rate of rise of reverse voltage		10000	V/μs

* : $\frac{dP_{tot}}{dT_j} < \frac{1}{R_{th}(j-a)}$ thermal runaway condition for a diode on its own heatsink

STPS2L25U

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-l)}$	Junction to lead	25	°C/W

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Tests Conditions	Tests Conditions	Min.	Typ.	Max.	Unit
I_R^*	Reverse leakage current	$T_j = 25^\circ\text{C}$	$V_R = V_{RRM}$		90	μA
		$T_j = 125^\circ\text{C}$		15	30	mA
V_F^*	Forward voltage drop	$T_j = 25^\circ\text{C}$	$I_F = 2\text{ A}$		0.45	V
		$T_j = 125^\circ\text{C}$		0.325	0.375	
		$T_j = 25^\circ\text{C}$	$I_F = 4\text{ A}$		0.53	
		$T_j = 125^\circ\text{C}$		0.43	0.51	

Pulse test : * $t_p = 380\text{ }\mu\text{s}$, $\delta < 2\%$

To evaluate the maximum conduction losses use the following equation :

$$P = 0.24 \times I_{F(AV)} + 0.068 I_{F(RMS)}^2$$

Fig. 1: Average forward power dissipation versus average forward current.

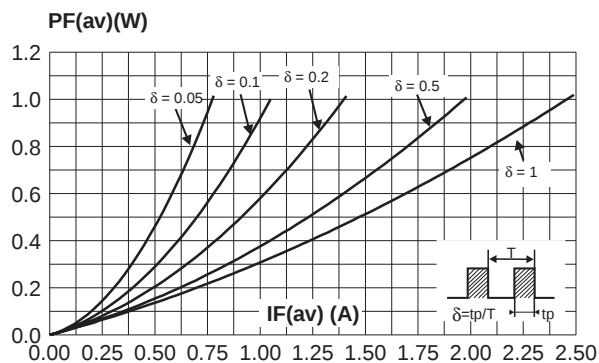


Fig. 3: Normalized avalanche power derating versus pulse duration.

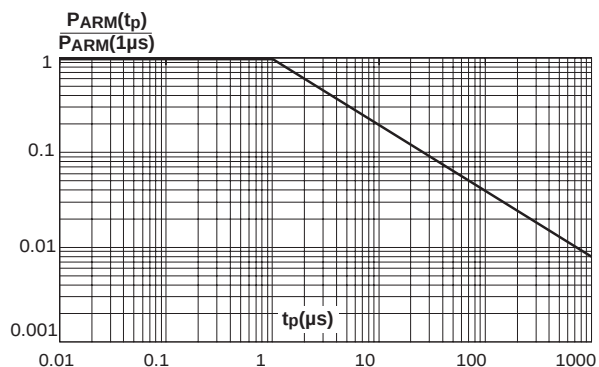


Fig. 2: Average forward current versus ambient temperature ($\delta=0.5$).

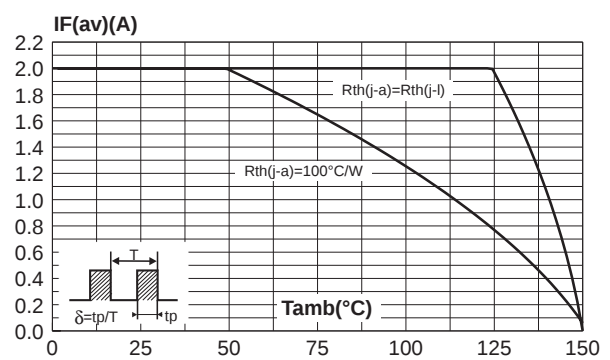


Fig. 4: Normalized avalanche power derating versus junction temperature.

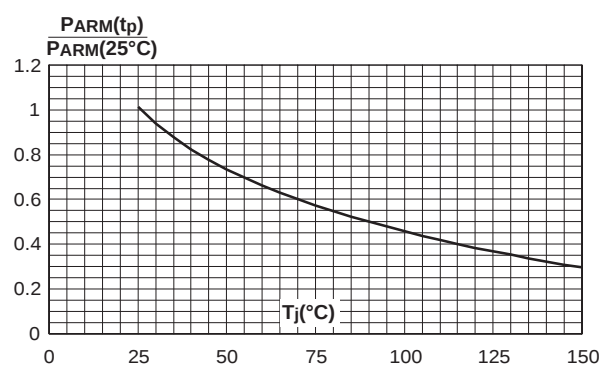


Fig. 5: Non repetitive surge peak forward current versus overload duration (maximum values).

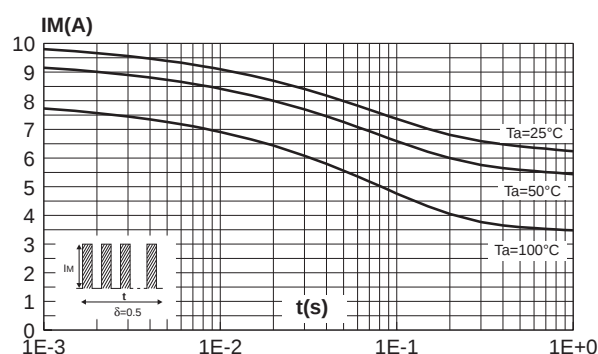


Fig. 6: Relative variation of thermal impedance junction to ambient versus pulse duration.

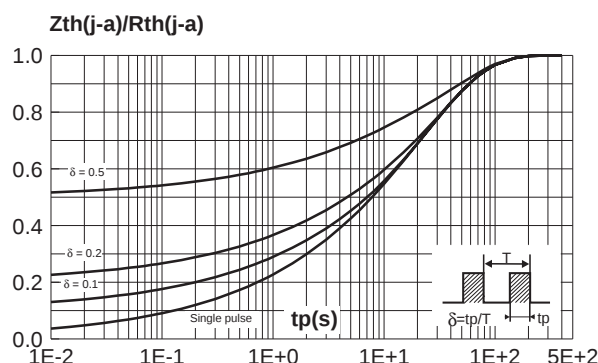


Fig. 7: Reverse leakage current versus reverse voltage applied (typical values).

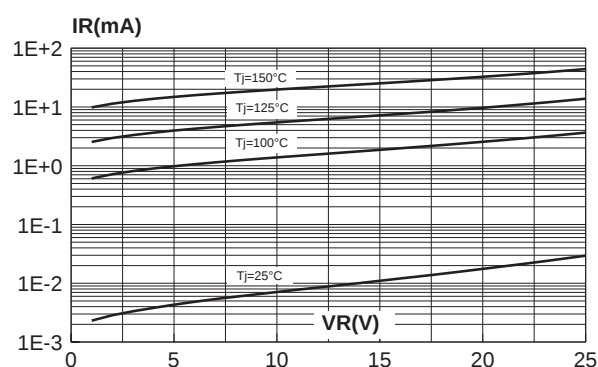


Fig. 8: Junction capacitance versus reverse voltage applied (typical values).

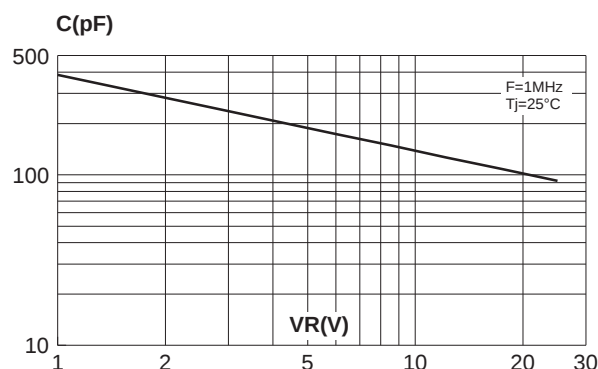


Fig. 9: Forward voltage drop versus forward current (maximum values).

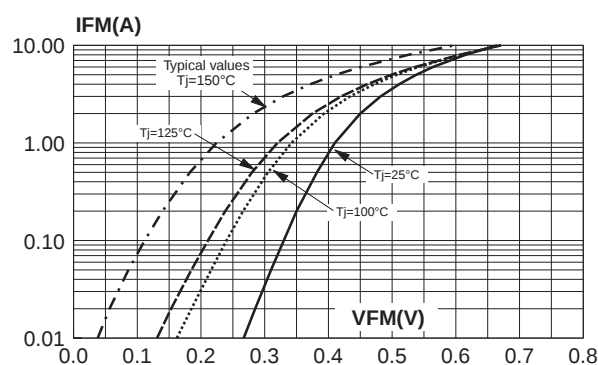
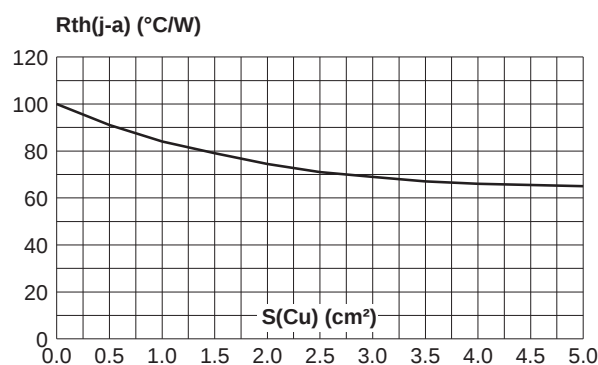


Fig. 10: Thermal resistance junction to ambient versus copper surface under each lead (Epoxy printed circuit board FR4, copper thickness:



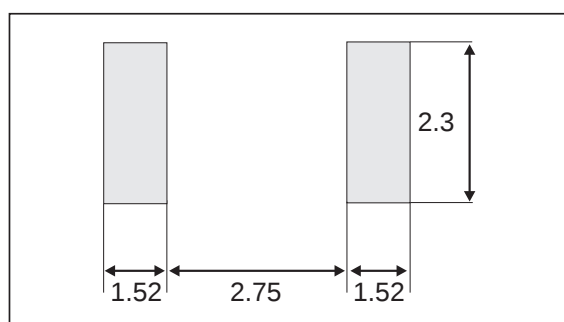
STPS2L25U

PACKAGE MECHANICAL DATA

SMB

REF.	DIMENSIONS			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A1	1.90	2.45	0.075	0.096
A2	0.05	0.20	0.002	0.008
b	1.95	2.20	0.077	0.087
c	0.15	0.41	0.006	0.016
E	5.10	5.60	0.201	0.220
E1	4.05	4.60	0.159	0.181
D	3.30	3.95	0.130	0.156
L	0.75	1.60	0.030	0.063

FOOT PRINT DIMENSIONS (in millimeters)



Ordering type	Marking	Package	Weight	Base qty	Delivery mode
STPS2L25U	G23	SMB	0.107g	2500	Tape & reel

- BAND INDICATES CATHODE
- EPOXY MEETS UL94,V0

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